SOT23-3 P MOS P- CHANNEL MOSFET in a SOT23-3 Plastic Package.

$V_{DS\ (}V) = -30V$

$I_D = -4.2$ A ($V_{GS} = -10V$)

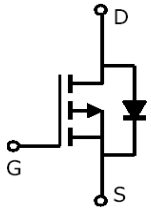
$R_{DS(ON)} < 60m\Omega$ ($V_{GS} = -10V$)

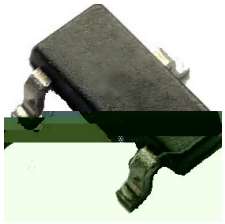
$R_{DS(ON)} < 65m\Omega$ ($V_{GS} = -4.5V$)

$R_{DS(ON)} < 120m\Omega$ ($V_{GS} = -2.5V$)

Halogen free product.

This device is suitable for use as a load switch or in PWM applications.

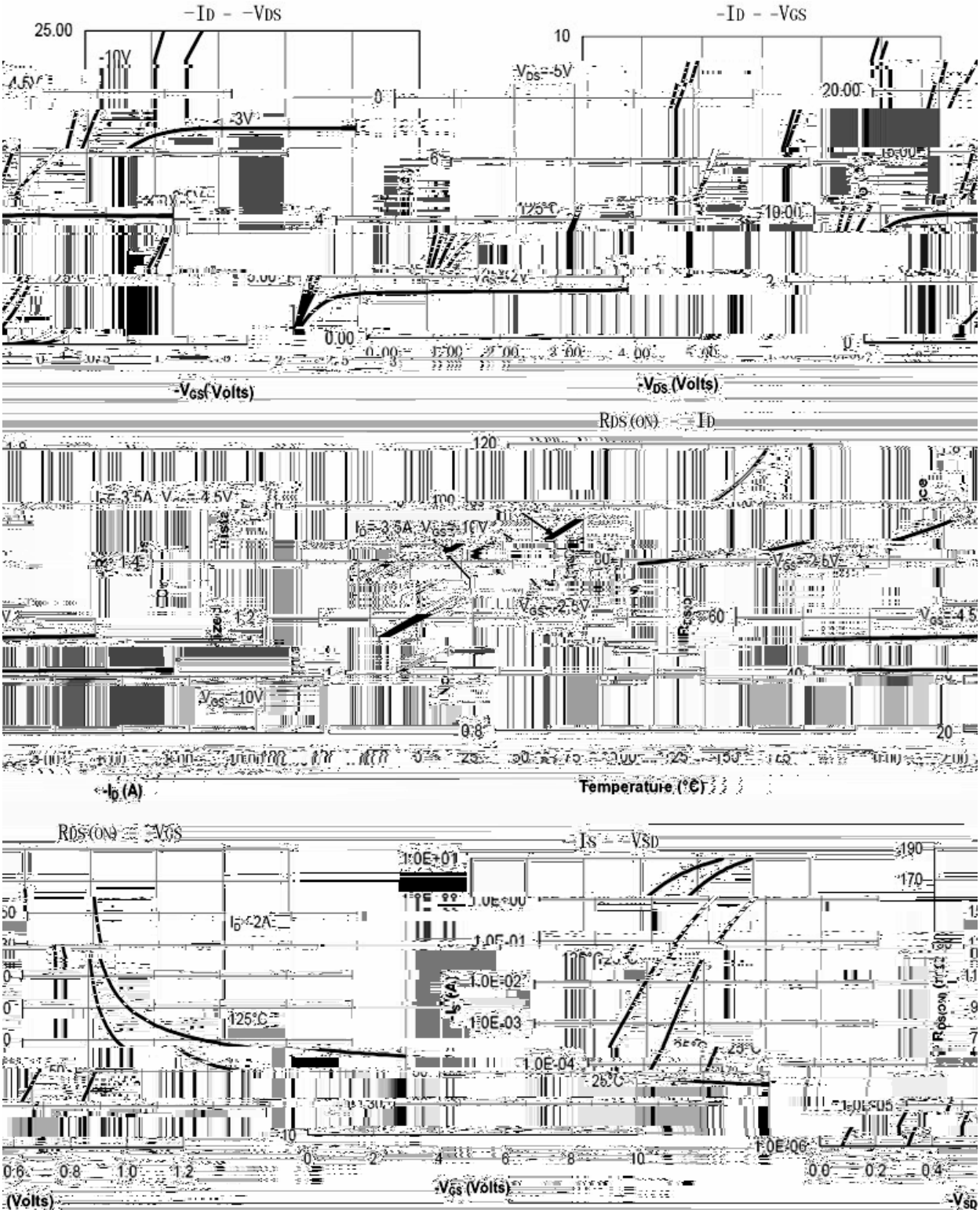


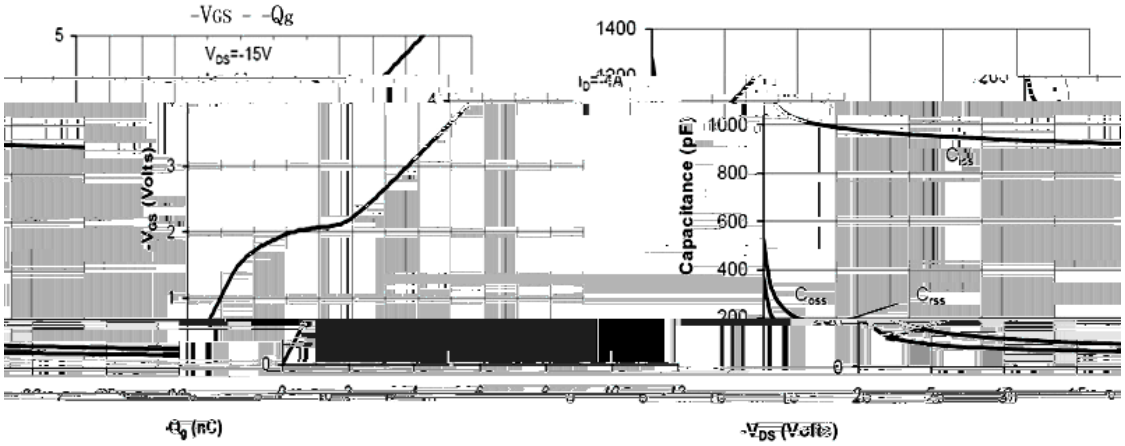


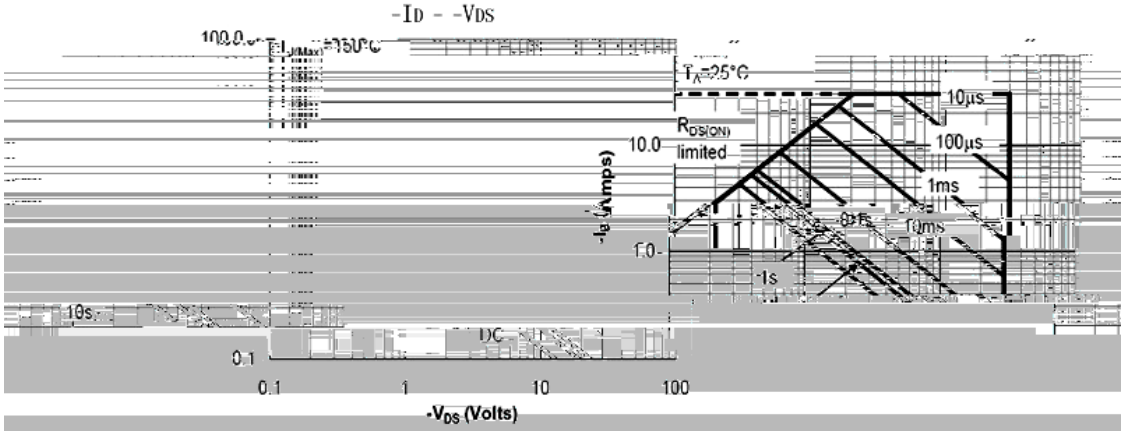
PIN1 G PIN 2 S PIN 3 D

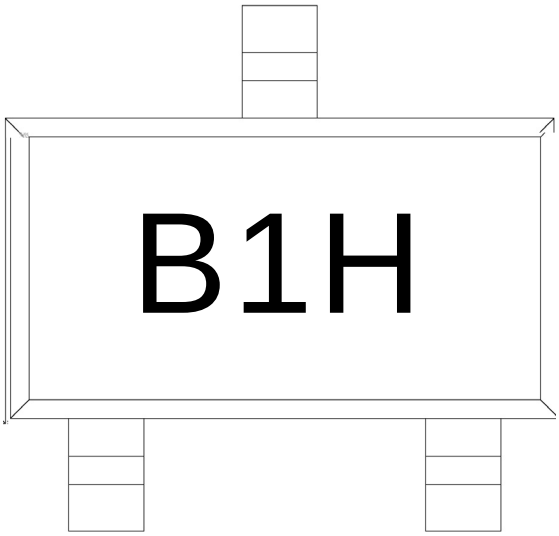
Marking	B1H

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit


-ID - -VDS
-ID - -VGS
-VGS(Volts)
-VDS (Volts)
RDS(ON) - ID
Temperature (°C)
-ID (A)
RDS(ON) - VGS
IS - VSD
-VGS (Volts)
-VSD
(Volts)


-VGS - -Qg
VDS=-15V
-VGS (Volts)
-Qg (nC)
Capacitance (pF)
Ciss
Coss
Crss
-VDS (Volts)


-ID - -VDS
TA=25°C
RDS(ON) limited
10µs
100µs
1ms
10ms
1s
10s
DC
-ID (Amps)
-VDS (Volts)



B1

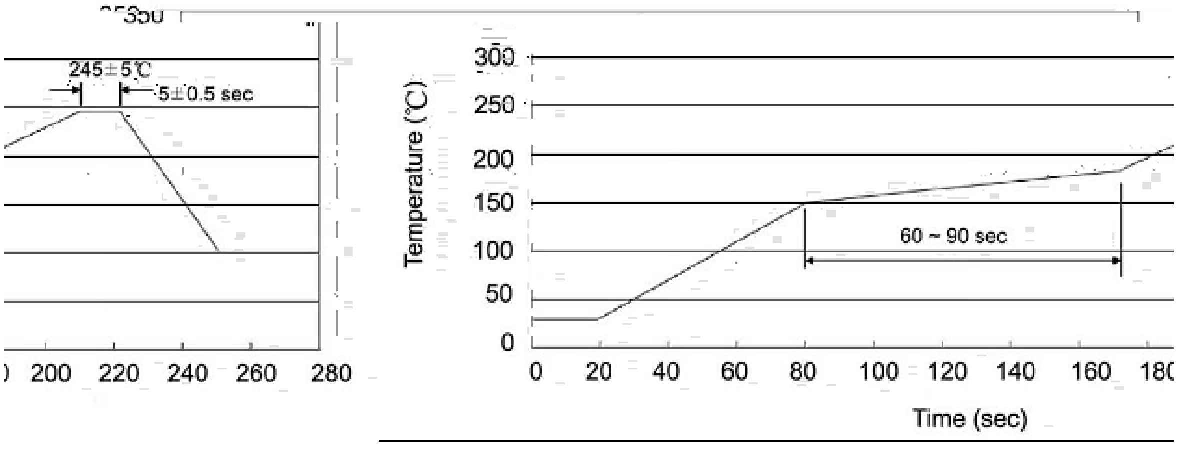
H

Note:

B1: Product Type Code.

H: Company Code.

Wh p shrdwxrh Prr iioh irr IU Uhiorw Vroghriq j+Pe-Frhh,



	Note:
1 150 180 60 90sec;	1.Preheating:150~180 , Time:60~90sec.
2 245±5 5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ REEL